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# **FDS6574A**

# 20V N-Channel PowerTrench<sup>ò</sup> MOSFET

### **General Description**

This N-Channel MOSFET has been designed specifically to improve the overall efficiency of DC/DC converters using either synchronous or conventional switching PWM controllers. It has been optimized for low gate charge, low R<sub>DS(ON)</sub> and fast switching speed.

## **Applications**

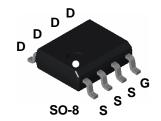
DC/DC converter

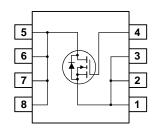


### **Features**

• 16 A, 20 V.  $R_{DS(ON)} = 6 \text{ m}\Omega \text{ @ } V_{GS} = 4.5 \text{ V}$   $R_{DS(ON)} = 7 \text{ m}\Omega \text{ @ } V_{GS} = 2.5 \text{ V}$   $R_{DS(ON)} = 9 \text{ m}\Omega \text{ @ } V_{GS} = 1.8 \text{ V}$ 

- · Low gate charge
- High performance trench technology for extremely low  $R_{\text{DS}(\text{ON})}$
- · High power and current handling capability
- · RoHS Compliant





# Absolute Maximum Ratings T<sub>A</sub>=25°C unless otherwise noted

Symbol	Parameter		Ratings	Units
V <sub>DSS</sub>	Drain-Source Voltage		20	V
V <sub>GSS</sub>	Gate-Source Voltage		± 8	V
I <sub>D</sub>	Drain Current - Continuous	(Note 1a)	16	А
	- Pulsed		80	
P <sub>D</sub>	Power Dissipation for Single Operation	(Note 1a)	2.5	W
		(Note 1b)	1.2	
		(Note 1c)	1.0	
$T_J$ , $T_{STG}$	Operating and Storage Junction Temperature Range		-55 to +175	°C

# **Thermal Characteristics**

$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	(Note 1a)	50	°C/W
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	(Note 1)	25	°C/W

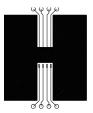
**Package Marking and Ordering Information** 

Device Marking	Device	Reel Size	Tape width	Quantity
FDS6574A	FDS6574A	13"	12mm	2500 units

Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
Off Char	acteristics	I	1			
BV <sub>DSS</sub>	Drain–Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, \qquad I_{D} = 250 \mu\text{A}$	20			V
ΔBV <sub>DSS</sub> ΔT <sub>J</sub>	Breakdown Voltage Temperature Coefficient	I <sub>D</sub> = 250 μA, Referenced to 25°C		10		mV/°C
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	$V_{DS} = 16 \text{ V}, \qquad V_{GS} = 0 \text{ V}$			1	μА
I <sub>GSSF</sub>	Gate–Body Leakage, Forward	$V_{GS} = 8 \text{ V}, \qquad V_{DS} = 0 \text{ V}$			100	nA
I <sub>GSSR</sub>	Gate-Body Leakage, Reverse	V <sub>GS</sub> = -8 V V <sub>DS</sub> = 0 V			-100	nA
On Char	acteristics (Note 2)					
$V_{\text{GS(th)}}$	Gate Threshold Voltage	$V_{DS} = V_{GS}$ , $I_D = 250 \mu A$	0.4	0.6	1.5	V
$\Delta V_{GS(th)} \over \Delta T_J$	Gate Threshold Voltage Temperature Coefficient	$I_D$ = 250 $\mu$ A, Referenced to 25°C		-2.7		mV/°C
$R_{DS(on)}$	Static Drain–Source On–Resistance	$V_{GS} = 4.5 \text{ V},  I_D = 16 \text{ A}$ $V_{GS} = 2.5 \text{ V},  I_D = 15 \text{ A}$ $V_{GS} = 1.8 \text{ V},  I_D = 13 \text{ A}$ $V_{GS} = 4.5 \text{ V},  I_D = 16 \text{ A}, T_J = 125 ^{\circ}\text{C}$		4 4.4 5 5.3	6 7 9	mΩ
I <sub>D(on)</sub>	On–State Drain Current	V <sub>GS</sub> = 4.5 V, V <sub>DS</sub> = 5 V	40			Α
<b>g</b> <sub>FS</sub>	Forward Transconductance	$V_{DS} = 5 \text{ V}, \qquad I_{D} = 16 \text{ A}$		115		S
Dynamic	Characteristics	•				
C <sub>iss</sub>	Input Capacitance	$V_{DS} = 10V$ , $V_{GS} = 0 V$ ,		7657		pF
Coss	Output Capacitance	f = 1.0 MHz 1432			pF	
C <sub>rss</sub>	Reverse Transfer Capacitance			775		pF
Switchir	ng Characteristics (Note 2)					
t <sub>d(on)</sub>	Turn-On Delay Time	$V_{DD} = 10 \text{ V}, \qquad I_D = 1 \text{ A},$		19.5	35	ns
t <sub>r</sub>	Turn-On Rise Time	$V_{GS} = 4.5 \text{ V}, R_{GEN} = 6 \Omega$		22	36	ns
t <sub>d(off)</sub>	Turn-Off Delay Time	7		173	277	ns
t <sub>f</sub>	Turn–Off Fall Time	7		82	131	ns
Q <sub>g</sub>	Total Gate Charge	$V_{DS} = 10 \text{ V},  I_{D} = 16 \text{ A},$		75	105	nC
Q <sub>gs</sub>	Gate-Source Charge	V <sub>GS</sub> = 4.5 V		9		nC
$Q_{gd}$	Gate-Drain Charge			17		nC
Drain-S	ource Diode Characteristics	and Maximum Ratings				
Is	Maximum Continuous Drain-Source				2.1	Α
$V_{SD}$	Drain–Source Diode Forward Voltage	V <sub>GS</sub> = 0 V, I <sub>S</sub> = 2.1 A (Note 2)		0.56	1.2	٧

### Notes:

 R<sub>8JA</sub> is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. R<sub>8JC</sub> is guaranteed by design while R<sub>8CA</sub> is determined by the user's board design.



a) 50°C/W when mounted on a 1in² pad of 2 oz copper



b) 105°C/W when mounted on a .04 in² pad of 2 oz copper



c) 125°C/W when mounted on a minimum pad.

Scale 1: 1 on letter size paper

2. Pulse Test: Pulse Width < 300 $\mu$ s, Duty Cycle < 2.0%

# **Typical Characteristics**

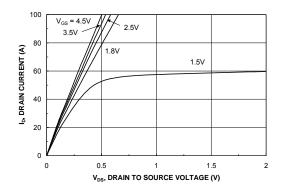


Figure 1. On-Region Characteristics.

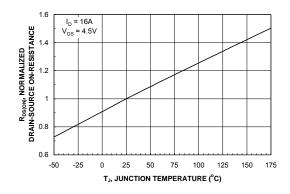


Figure 3. On-Resistance Variation with Temperature.

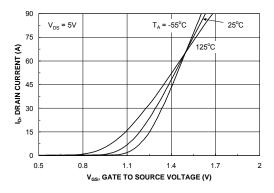


Figure 5. Transfer Characteristics.

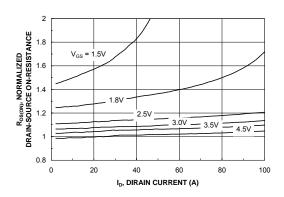


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

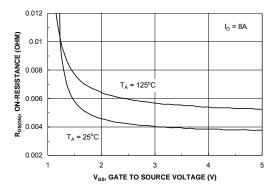


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

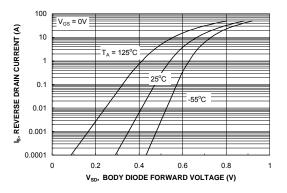
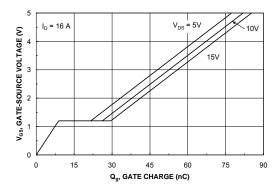


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

# **Typical Characteristics**



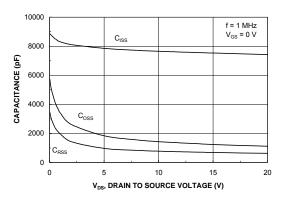
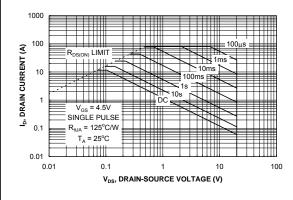


Figure 7. Gate Charge Characteristics.





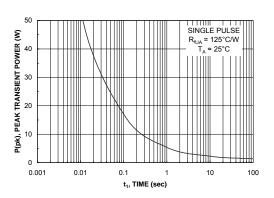


Figure 9. Maximum Safe Operating Area.

Figure 10. Single Pulse Maximum Power Dissipation.

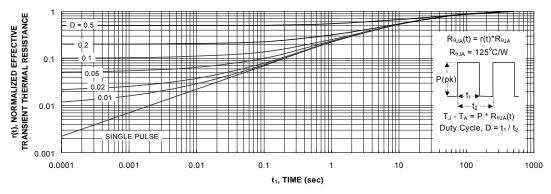


Figure 11. Transient Thermal Response Curve.

Thermal characterization performed using the conditions described in Note 1c. Transient thermal response will change depending on the circuit board design.





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